

Please add the following new claims:

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14. (New) A method for producing a mass flow sensor, the method comprising:
- forming a frame made at least in part by silicon;
  - forming a membrane held by the frame;
  - forming a metal layer above the frame, the metal layer including a first structure and a second structure;
  - forming a heating element by the first structure in the metal layer;
  - forming at least one temperature measurement element by the second structure in the metal layer; and
  - forming a moisture barrier arranged above the metal layer.
15. (New) The method according to claim 14, wherein the moisture barrier is formed at least in part by a nitride layer.
16. (New) The method according to claim 15, wherein the nitride layer includes a silicon nitride layer.
17. (New) The method according to claim 16, wherein the nitride layer is formed by an operation selected from the group consisting of a PECVD operation, a LPCVD operation, and a CVD operation.
18. (New) The method according to claim 14, further comprising:
- forming a CVD oxide layer directly below the metal layer.

**IN THE SPECIFICATION:**

Please replace the paragraph beginning on page 4, line 29, with the following new paragraph:

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--Electrically insulated structures are produced in platinum layer 10 by etching in a known way. The structures, each of which is provided with two terminals (not shown) to establish an